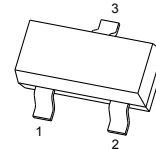


Plastic-Encapsulate MOSFETS

N-Channel 20-V(D-S) MOSFET

$V_{(BR)DSS}$	$R_{DS(on)}$	I_D Max
20V	0.013 Ω @ 4.5V	6.0A
	0.015 Ω @ 2.5V	

SOT-23



- 1.GATE
- 2.SOURCE
- 3.DRAIN

FEATURE

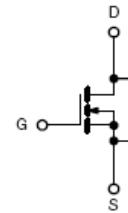
- TrenchFET Power MOSFET
- Excellent $R_{DS(on)}$
- Low Gate Charge
- High Power and Current Handling Capability
- Surface Mount Package

APPLICATION

- Load Switch
- Power Management

MARKING: 207N

Equivalent Circuit



ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	I_D	6	A
Pulsed Drain Current (note 1)	I_{DM}	25	A
Thermal Resistance from Junction to Ambient (note 2)	$R_{\theta JA}$	100	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55~+150	$^\circ\text{C}$
Lead Temperature for Soldering Purposes(1/8" from case for 10 s)	T_L	260	$^\circ\text{C}$

MOSFETS ELECTRICAL CHARACTERISTICS

T_a =25 °C unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
STATIC CHARACTERISTICS						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =250μA	20			V
Zero gate voltage drain current	I _{DSS}	V _{DS} =18V, V _{GS} = 0V			100	nA
Gate-body leakage current	I _{GSS}	V _{GS} =±12V, V _{DS} = 0V			±100	nA
Gate threshold voltage (note 3)	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	0.5		1.0	V
Drain-source on-resistance (note 3)	R _{DS(on)}	V _{GS} =4.5V, I _D =6A	9	13	14	mΩ
		V _{GS} =2.5V, I _D =5A	12	15	18	mΩ
Forward tranconductance (note 3)	g _{FS}	V _{DS} =5V, I _D =6A		10		S
Diode forward voltage (note 3)	V _{SD}	I _S =2.00A, V _{GS} = 0V			1.0	V
DYNAMIC CHARACTERISTICS (note4)						
Input Capacitance	C _{iss}	V _{DS} =10V, V _{GS} =0V, f =1MHz		615		pF
Output Capacitance	C _{oss}			150		pF
Reverse Transfer Capacitance	C _{rss}			120		pF
SWITCHING CHARACTERISTICS (note 4)						
Turn-on delay time	t _{d(on)}	V _{GS} =5V, V _{DS} =10V, R _L =1.4Ω, R _{GEN} =3Ω		7.2		ns
Turn-on rise time	t _r			13		ns
Turn-off delay time	t _{d(off)}			29		ns
Turn-off fall time	t _f			11		ns
Total Gate Charge	Q _g	V _{DS} =10V, V _{GS} =4.5V, I _D =6A		12		nC
Gate-Source Charge	Q _{gs}			1.2		nC
Gate-Drain Charge	Q _{gd}			3.0		nC

Notes :

- 1.Repetitive rating: Pluse width limited by maximum junction temperature
- 2.Surface Mounted on FR4 board, t ≤10 sec.
3. Pulse test : Pulse width ≤300μs, duty cycle ≤2%.
4. Guaranteed by design, not subject to production.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

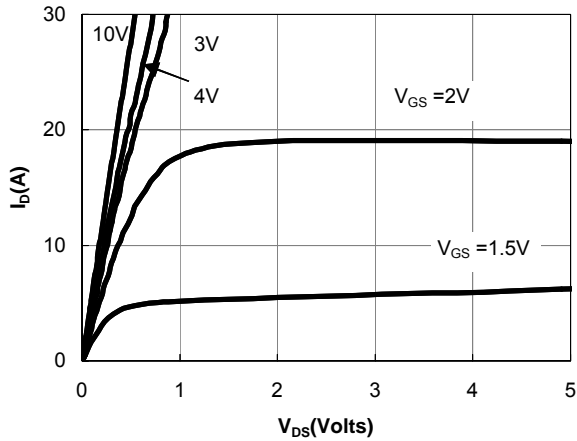


Figure 1: On-Regions Characteristic CS

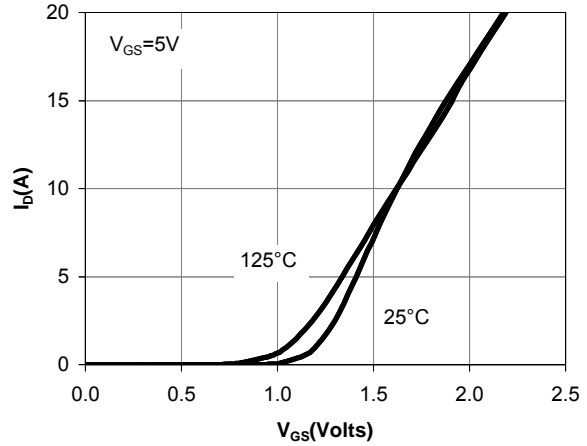


Figure 2: Transfer Characteristics

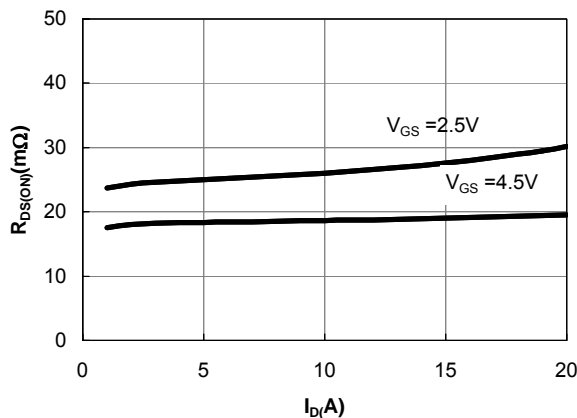


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

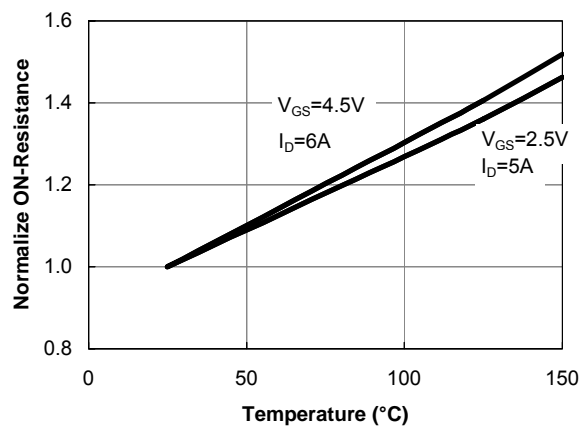


Figure 4: On-Resistance vs. Junction Temperature

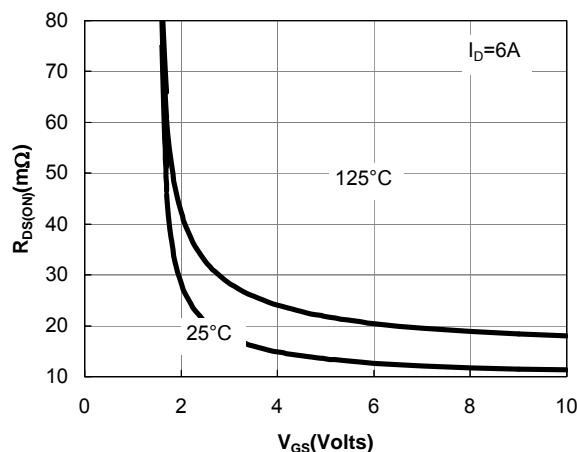


Figure 5: On-Resistance vs. Gate-Source Voltage

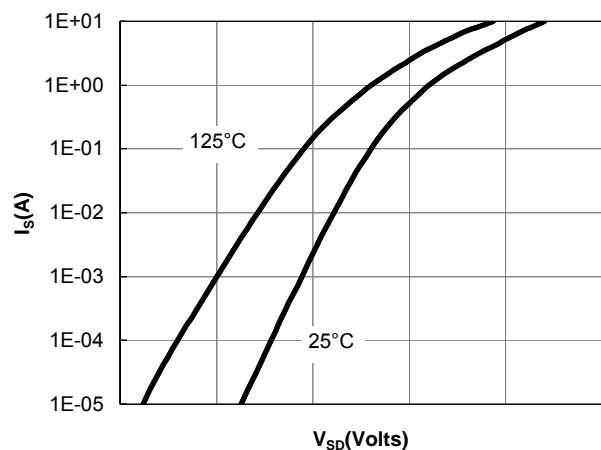


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

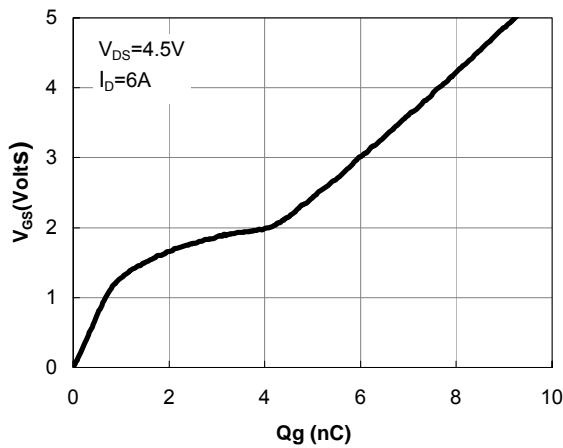


Figure 7: Gate-Charge Characteristics

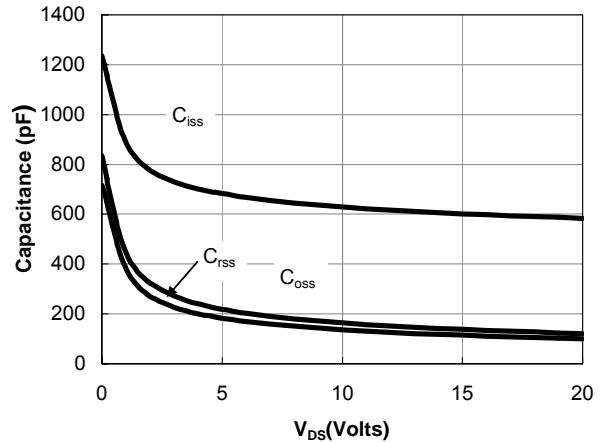


Figure 8: Capacitance Characteristics

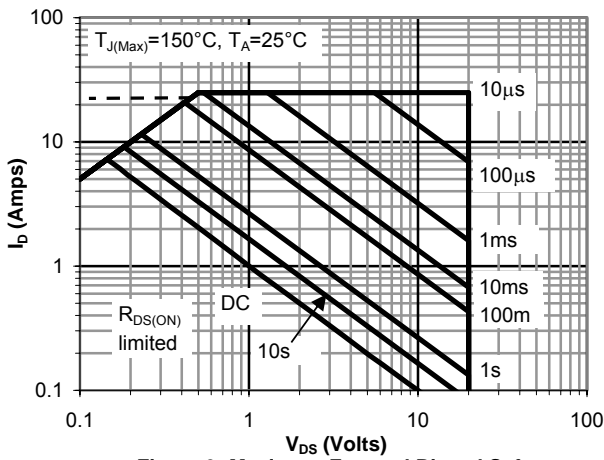


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

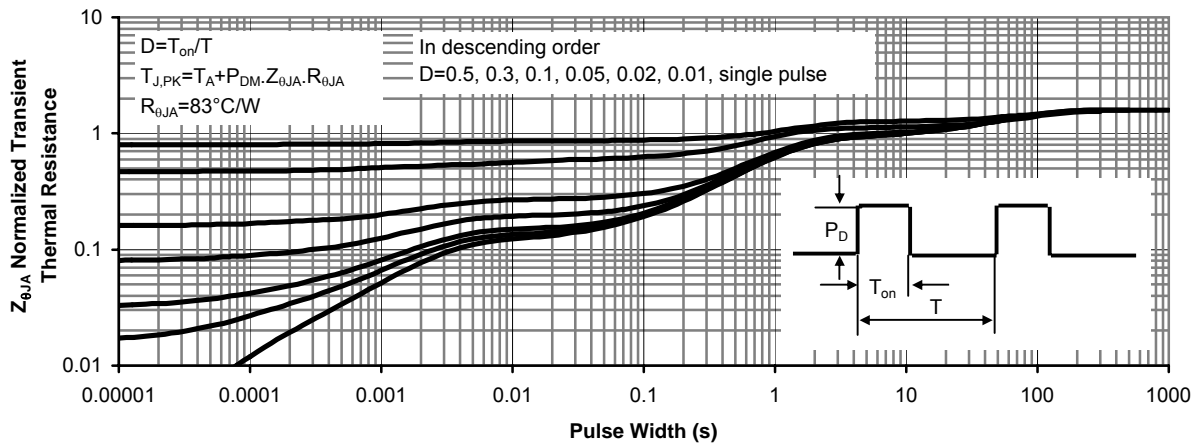
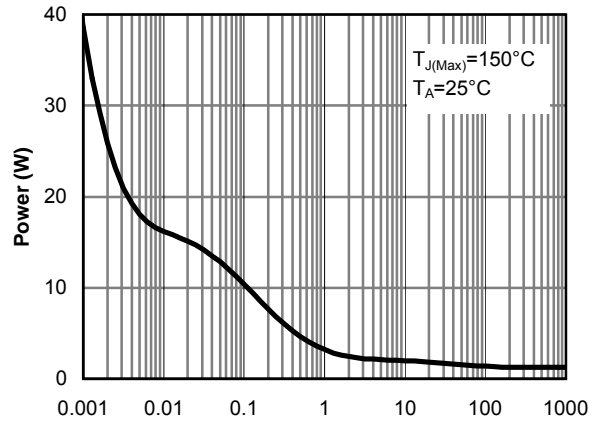
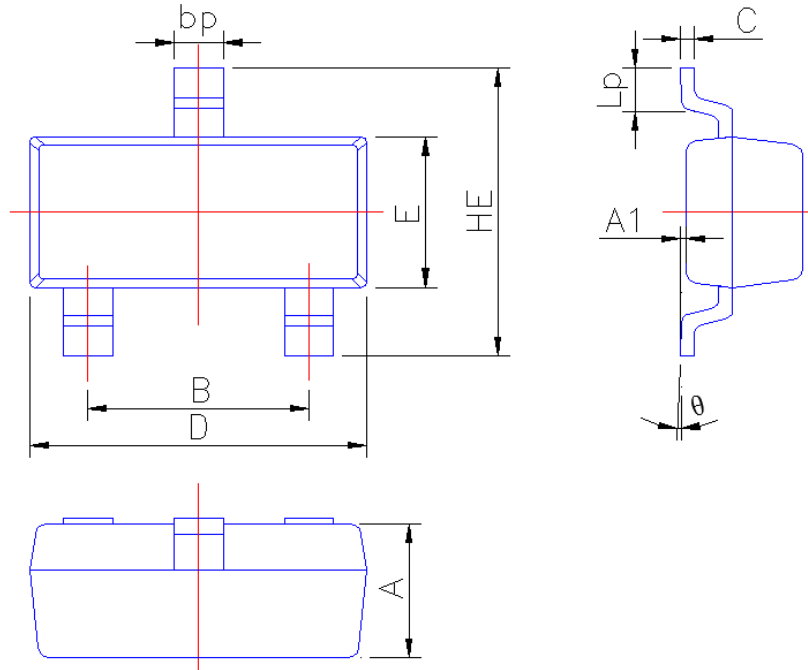


Figure 11: Normalized Maximum Transient Thermal Impedance

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



Symbol	Dimension in Millimeters	
	Min	Max
A	0.90	1.10
A1	0.013	0.100
B	1.80	2.00
bp	0.35	0.50
C	0.09	0.150
D	2.80	3.00
E	1.20	1.40
HE	2.20	2.80
Lp	0.20	0.50
θ	0°	5°